

DSA60C60PB

preliminary

 $V_{RRM} = 60 V$

 $I_{FAV} = 2x \quad 30 A$

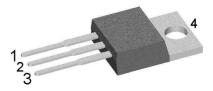
 $V_F = 0.77 V$

High Performance Schottky Diode Low Loss and Soft Recovery Common Cathode

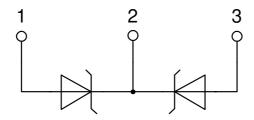
Schottky Diode Gen²

Part number

DSA60C60PB



Backside: cathode



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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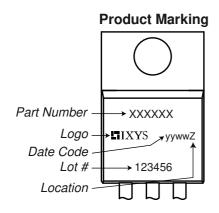
Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockir	ng voltage	$T_{VJ} = 25^{\circ}C$			60	V
V _{RRM}	max. repetitive reverse blocking vo	ltage	$T_{VJ} = 25^{\circ}C$			60	V
IR	reverse current, drain current	V _R = 60 V	$T_{VJ} = 25^{\circ}C$			450	μΑ
		$V_R = 60 \text{ V}$	$T_{VJ} = 125^{\circ}C$			5	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			0.92	V
		$I_F = 60 \text{ A}$				1.17	٧
		$I_F = 30 \text{ A}$	T _{vJ} = 125°C			0.77	٧
		$I_F = 60 \text{ A}$				1.00	٧
I _{FAV}	average forward current	T _C = 155°C	T _{vJ} = 175°C			30	Α
		rectangular d = 0.5					-
V _{F0}	threshold voltage		$T_{VJ} = 175$ °C			0.49	V
\mathbf{r}_{F}	slope resistance	ss calculation only				6.8	mΩ
R _{thJC}	thermal resistance junction to case					0.85	K/W
R _{thCH}	thermal resistance case to heatsing	k			0.5		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			175	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			450	Α
CJ	junction capacitance	$V_R = 12 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		449		pF



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Package	Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal 10			35	Α	
T _{VJ}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				2		g	
M _D	mounting torque		0.4		0.6	Nm	
F_c	mounting force with clip		20		60	Ν	



Part description

D = Diode

S = Schottky Diode

A = low VF

60 = Current Rating [A]

C = Common Cathode

60 = Reverse Voltage [V]

PB = TO-220AB (3)

Orderin	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standa	DSA60C60PB	DSA60C60PB	Tube	50	507143

Similar Part	Package	Voltage class	
DSA60C60HB	TO-247AD (3)	60	

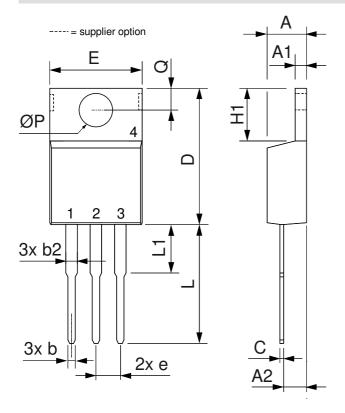
Equiva	lent Circuits for	Simulation	* on die level	$T_{VJ} = 175^{\circ}C$
$I \rightarrow V_0$)—R _o	Schottky		
V _{0 max}	threshold voltage	0.49		V
$R_{0 max}$	slope resistance *	3.6		mΩ





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Outlines TO-220



Dim.	Millimeter		Incl	nes
	Min.	Max.	Min.	Max.
Α	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
С	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
е	2.54	BSC	0.100	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125

